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HEEYONG PARK ET AL  
FIS920000404US1

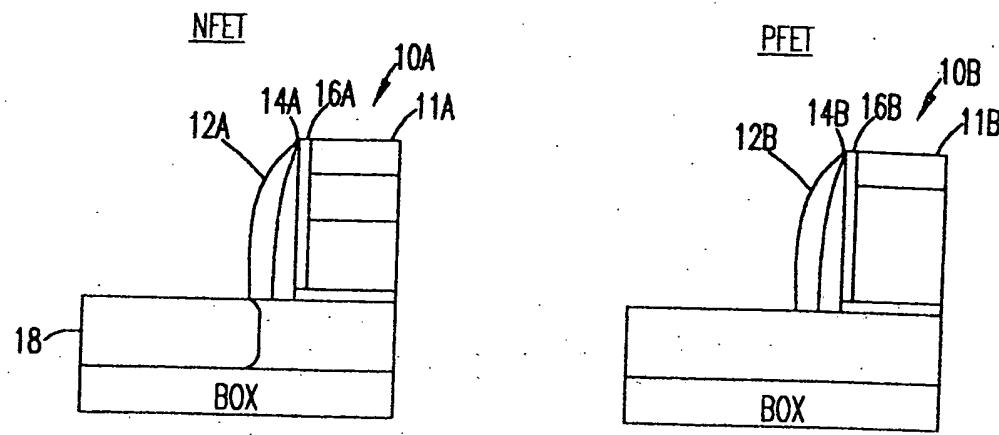


FIG. 1

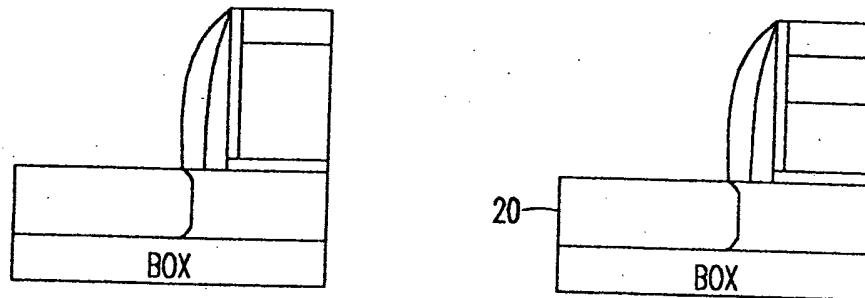


FIG. 2

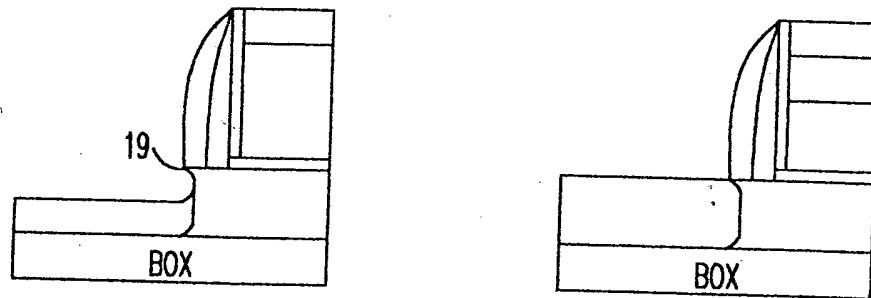


FIG. 3

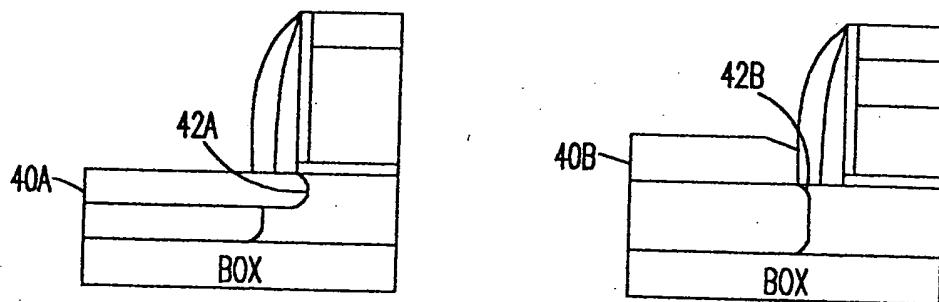


FIG. 4

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**TRANSMITTAL OF FORMAL DRAWINGS**Docket No.  
00750425AA

In Re Application Of: H. Park, et al.

Serial No.

09/924,318

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Art Unit

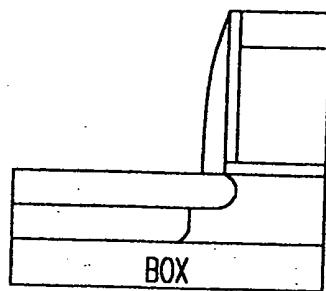
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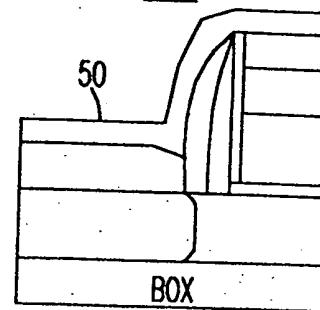


FIG. 5

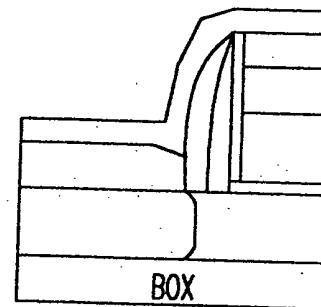
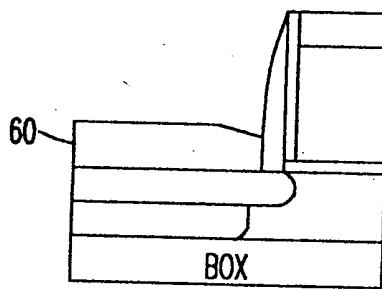


FIG. 6

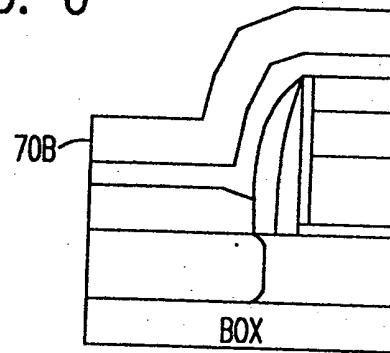
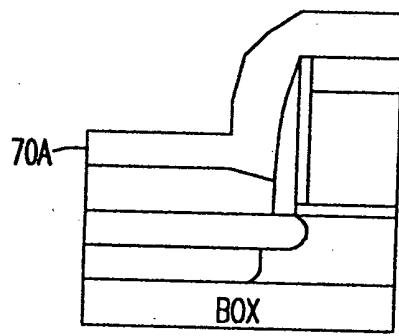


FIG. 7

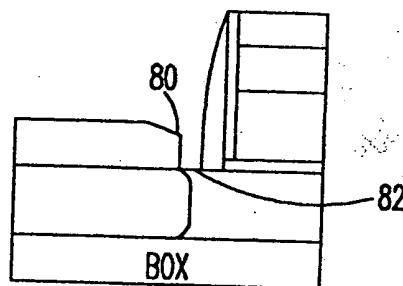
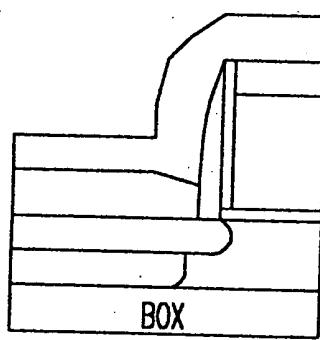


FIG. 8

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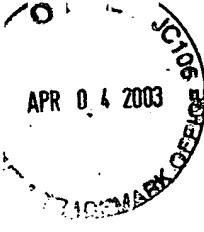
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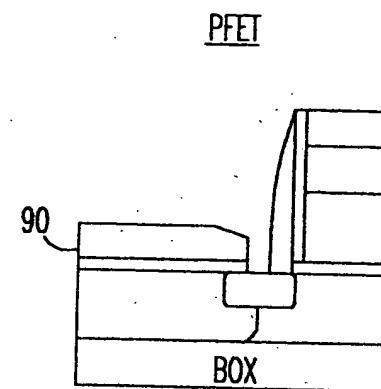
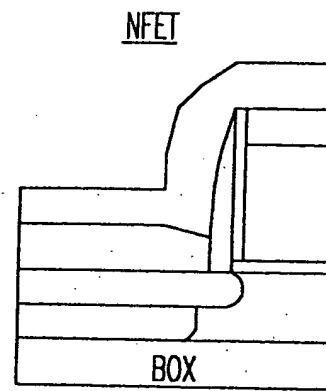


FIG. 9

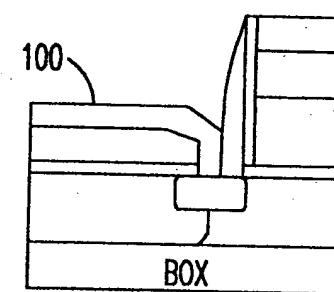
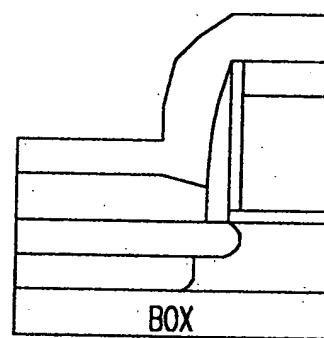


FIG. 10

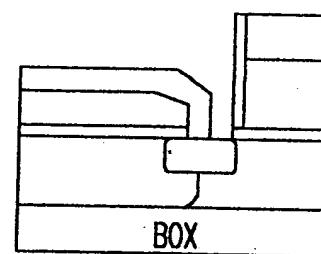
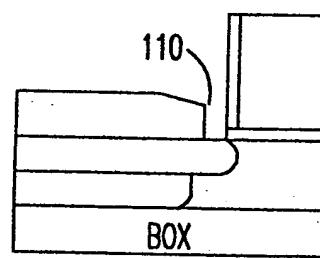


FIG. 11

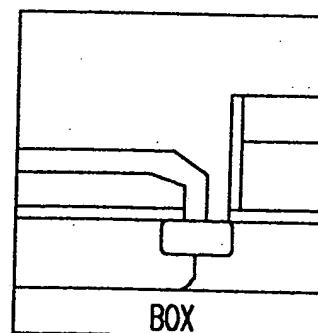
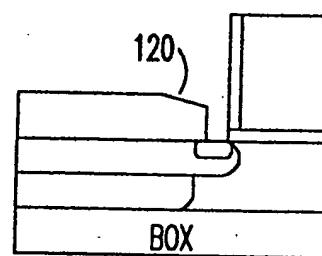


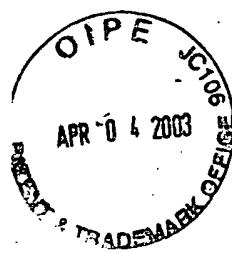
FIG. 12

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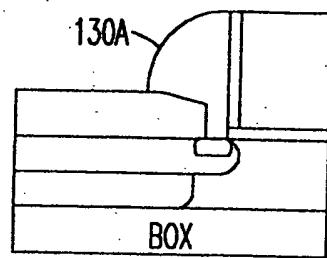
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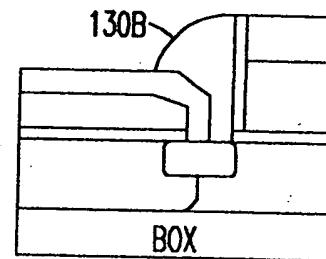


FIG. 13

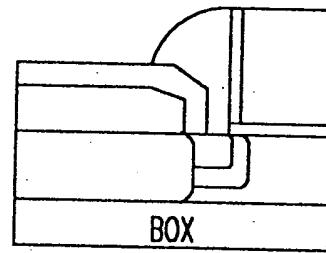
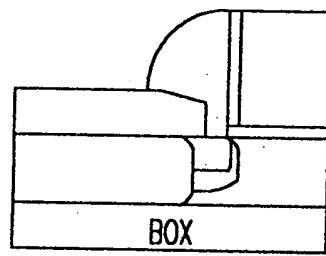


FIG. 14

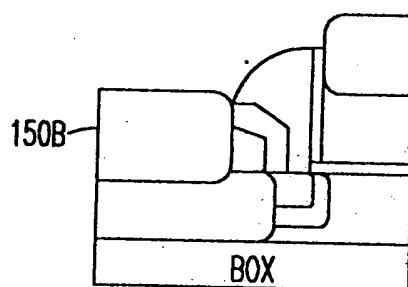
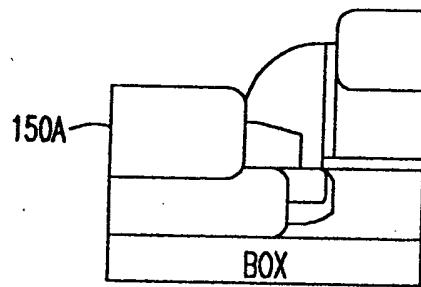


FIG. 15

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